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Abstract of Disclosure

An object of the present invention is to provide a semiconductor device capable of radiating electron-beams only to a desired region without forming a layer for restricting the radiating rays. A source electrode 22 made of aluminum prevents the generation of bremsstrahlung even when the electron-beams are radiated to the source electrode in a exposed condition. Also, the source electrode having an opening 25 at above of a crystal defect region 11 is used as a mask when the electron-beams are radiated thereto. That is the source electrode made of aluminum can be used both as a wiring and a mask for the radiating rays.

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